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INFORMATION DISCLOSURE STATEMENT BY APPLICANT  (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT Leinikka et al.	
		FILING DATE March 25, 2004	GROUP <del>2042</del>

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
	101. Martensson et al., "Atomic Layer Epitaxy of Copper and Tantalum," <u>Chemical Vapor Deposition</u> , Vol. 3, No. 1, pp. 45-50, (1997)
	102. Martensson et al., "CU(THD) <sub>2</sub> As Copper Source in Atomic Layer Epitaxy," <u>Electrochemical Society Proceedings</u> , Vol. 97-25, pp. 1529-1536, (1997)
	103. Martensson, "Use of atomic layer epitaxy for fabrication of Si/TiN/Cu structures," <u>J. Vac. Sci. Technol. B</u> , Vol. 17, No. 5, pp. 2122-2128, (Sept./Oct. 1999)
	104. Min, Jae-Sik, Young Woong Son, Won-Gu Kang, Soung-Soon Chun, and Sang-Won Kang, "Atomic Layer Deposition of TiN Films by Alternate Supply of Tetrakis (ethylmethylamino)-Titanium and Ammonia," <u>Jpn. J. Appl. Phys.</u> , Vol. 37, pp. 4999-5004, (1998).
	105. Min, Jae-Sik, Young-Woong Son, Won-Gu Kang, and Sang-Won Kang, "Atomic Layer Deposition of TiN Thin Films by Sequential Introduction of Ti Precursor and HN <sub>3</sub> ," <u>Mat. Res. Soc. Symp. Proc.</u> , Vol. 514, pp. 337-342, (1998).
	106. Nakajima, Tsuyoshi and Toru Shirasaki, "Chemical Vapor Deposition of Tungsten Carbide, Molybdenum Carbide Nitride, and Molybdenum Nitride Films," <u>J. Electrochem. Soc.</u> , Vol. 144, No. 6, pp. 2096-2100, (June 1997)
	107. Polyakov et al., "Growth of GaBN Ternary Solutions by Organometallic Vapor Phase Epitaxy," <u>Journal of Electronic Materials</u> , Vol. 26, No. 3, pp. 237-242, (1997)
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	109. Ritala, Mikko, Markku Leskelä, Eero Rauhalä, and Janne Jokinen, "Atomic Layer Epitaxy Growth of TiN Thin Films from TiL <sub>4</sub> and NH <sub>3</sub> ," <u>J. Electrochem. Soc.</u> , Vol. 145, No. 8, pp. 2914-2920, (August 1998)
	110. Ritala et al., "Effects of intermediate zinc pulses on properties of TiN and NbN films deposited by atomic layer epitaxy," <u>Appl. Surf. Sci.</u> , 120:199-212 (1997).
	111. Ritala et al., "Perfectly conformal TiN and Al <sub>2</sub> O <sub>3</sub> films deposited by atomic layer deposition," <u>Chem. Vapor Deposition</u> , 5:7-9 (1999).
	112. Ryu et al., "Barriers for copper interconnections," <u>Solid State Technology</u> , April, 53 (1999).
	113. Sherman et al., "Plasma enhanced atomic layer deposition of Ta for diffusion barrier applications," AVS 46 <sup>th</sup> International Symposium, Paper TF-TuM5 (abstract), (October 26, 1999), Seattle, WA.
	114. Yang et al., "Atomic Layer Deposition of Tungsten Film from WF <sub>6</sub> /B <sub>2</sub> H <sub>6</sub> : Nucleation Layer for Advanced Semiconductor Devices," Advanced Metallization Conference 2001 (AMC 2001), Conference Proceedings ULSI XVII@2002 Materials Research Society, pp. 655-660.

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ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /AC/ (03/14/2008)

EXAMINER /Alonzo Chambliss/ (03/14/2008)	DATE CONSIDERED
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